Taiwan Semiconductor

30mA, 40V Low V_F SMD Schottky Barrier Diode

FEATURES

- Low power loss, high current capability, low V_F
- Surface mount device type
- Moisture sensitivity level: level 1, per J-STD-020
- RoHS Compliant

APPLICATIONS

- Switching mode power supply (SMPS)
- Adapters
- Lighting application
- On-board DC/DC converter

MECHANICAL DATA

- Case: SOD-323F
- Molding compound meets UL 94V-0 flammability rating
- Terminal: Matte tin plated leads, solderable per J-STD-002
- Meet JESD 201 class 1A whisker test
- Polarity: Indicated by cathode band
- Weight: 4.60mg (approximately)

KEY PARAMETERS			
PARAMETER	R VALUE UNI		
I _F	30	mA	
V _{RRM}	40	V	
V _F at I _F = 1mA	0.37	V	
T _{J MAX}	125	°C	
Package	SOD-323F		
Configuration	Single die		









ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)				
PARAMETER		SYMBOL	RB751V-40WS	UNIT
Marking code on the device			S8	
Power Dissipation		P _D	200	mW
Repetitive Peak Reverse Voltage		V _{RRM}	40	V
Reverse Voltage		V _R	30	V
Forward current		I _F	30	mA
Non-repetitive peak forward surge current	60Hz for 1 Cyc.	I _{FSM}	0.2	А
Junction temperature range		TJ	-40 to +125	°C
Storage temperature range		T _{STG}	-40 to +125	°C



THERMAL PERFORMANCE			
PARAMETER	SYMBOL	ТҮР	UNIT
Junction-to-ambient thermal resistance	R _{eja}	500	°C/W

ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)					
PARAMETER	CONDITIONS	SYMBOL	ТҮР	MAX	UNIT
Forward Voltage ⁽¹⁾	I _F = 1mA	V _F	-	0.37	V
Reverse current @ rated $V_R^{(2)}$	V _R = 30V	I _R	-	0.50	μA
Junction capacitance	$1MHz, V_R = 1V$	CJ	2	-	pF

Notes:

1. Pulse test with PW = 0.3ms

2. Pulse test with PW = 30ms

ORDERING INFORMATION			
ORDERING CODE ⁽¹⁾	PACKAGE	PACKING	
RB751V-40WS RR	SOD-323F	3K / 7" Reel	
RB751V-40WS RRG	SOD-323F	3K / 7" Reel	
RB751V-40WS R9	SOD-323F	10K / 13" Reel	
RB751V-40WS R9G	SOD-323F	10K / 13" Reel	

Notes:

1. "G" means green compound (halogen-free according to IEC 61249-2-21)



CHARACTERISTICS CURVES

(T_A = 25°C unless otherwise noted)

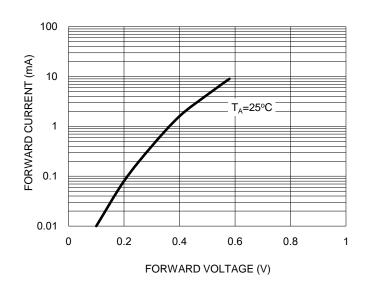


Fig.1 Typical Forward Characteristics

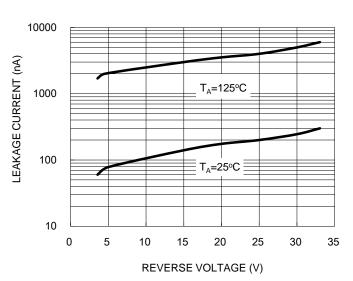


Fig.2 Typical Reverse Characteristics



Fig.3 Typical Junction Capacitance

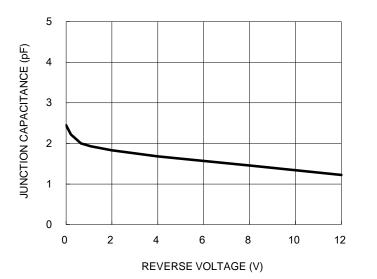
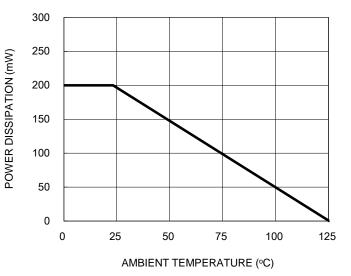
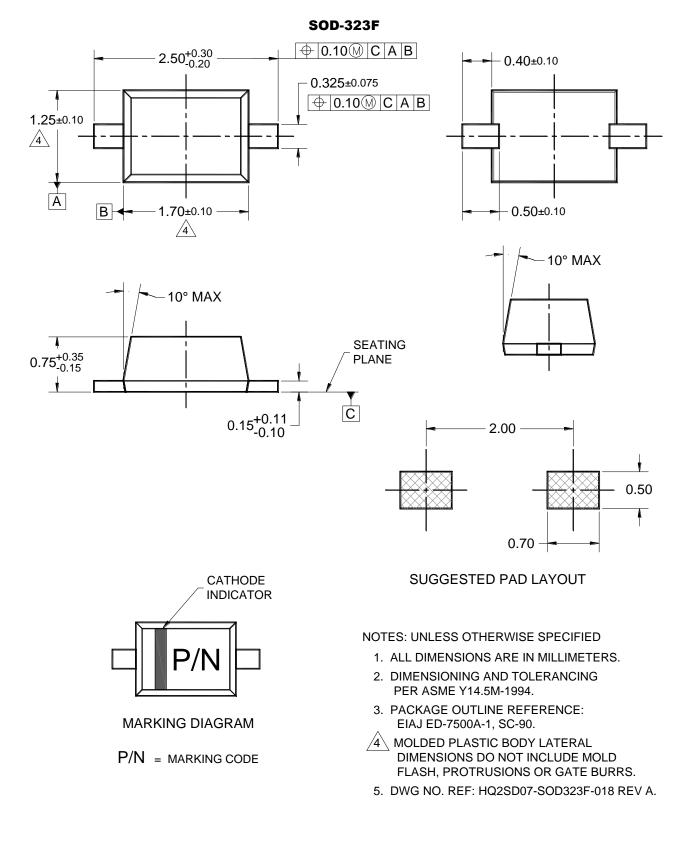


Fig.4 Power Dissipation Curve





PACKAGE OUTLINE DIMENSIONS





Taiwan Semiconductor

Notice

Specifications of the products displayed herein are subject to change without notice. TSC or anyone on its behalf assumes no responsibility or liability for any errors or inaccuracies.

Purchasers are solely responsible for the choice, selection, and use of TSC products and TSC assumes no liability for application assistance or the design of Purchasers' products.

Information contained herein is intended to provide a product description only. No license, express or implied, to any intellectual property rights is granted by this document. Except as provided in TSC's terms and conditions of sale for such products, TSC assumes no liability whatsoever, and disclaims any express or implied warranty, relating to sale and/or use of TSC products including liability or warranties relating to fitness for a particular purpose, merchantability, or infringement of any patent, copyright, or other intellectual property right.

The products shown herein are not designed for use in medical, life-saving, or life-sustaining applications. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify TSC for any damages resulting from such improper use or sale.